

## EasyPACK™ module with TRENCHSTOP™ IGBT7 and emitter controlled 7 diode and PressFIT / NTC

### Features

- Electrical features
  - $V_{CES} = 1200\text{ V}$
  - $I_{C\text{ nom}} = 100\text{ A} / I_{CRM} = 200\text{ A}$
  - TRENCHSTOP™ IGBT7
  - Low  $V_{CE,sat}$
  - Overload operation up to  $175^{\circ}\text{C}$
- Mechanical features
  - PressFIT contact technology
  - High power density
  - Compact design
  - $\text{Al}_2\text{O}_3$  substrate with low thermal resistance
  - 2.5 kV AC 1 minute insulation



Typical appearance

### Potential applications

- Auxiliary inverters
- Servo drives
- Air conditioning
- Motor drives
- UPS systems

### Product validation

- Qualified for industrial applications according to the relevant tests of IEC 60747, 60749 and 60068

### Description

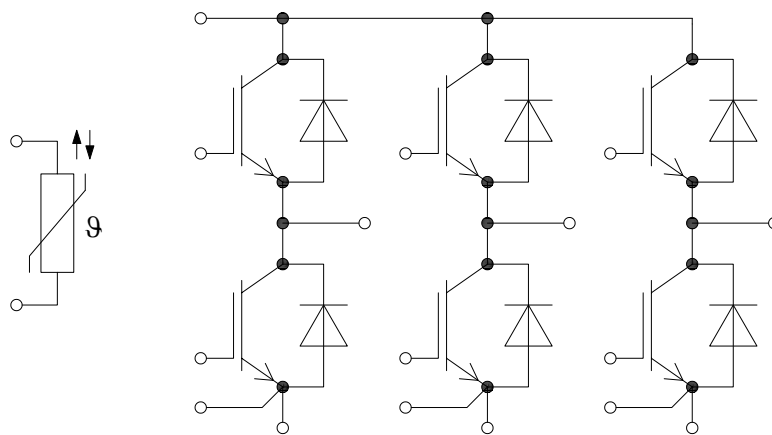


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## 1 Package

**Table 1** Insulation coordination

| Parameter                           | Symbol      | Note or test condition                         | Values    | Unit |
|-------------------------------------|-------------|------------------------------------------------|-----------|------|
| Isolation test voltage              | $V_{ISOL}$  | RMS, $f = 50 \text{ Hz}$ , $t = 1 \text{ min}$ | 2.5       | kV   |
| Internal isolation                  |             | basic insulation (class 1, IEC 61140)          | $Al_2O_3$ |      |
| Creepage distance                   | $d_{Creep}$ | terminal to heatsink                           | 11.5      | mm   |
| Creepage distance                   | $d_{Creep}$ | terminal to terminal                           | 6.3       | mm   |
| Clearance                           | $d_{Clear}$ | terminal to heatsink                           | 10.0      | mm   |
| Clearance                           | $d_{Clear}$ | terminal to terminal                           | 5.0       | mm   |
| Comparative tracking index          | $CTI$       |                                                | > 200     |      |
| Relative thermal index (electrical) | $RTI$       | housing                                        | 140       | °C   |

**Table 2** Characteristic values

| Parameter                                | Symbol        | Note or test condition             | Values |      |      | Unit |
|------------------------------------------|---------------|------------------------------------|--------|------|------|------|
|                                          |               |                                    | Min.   | Typ. | Max. |      |
| Stray inductance module                  | $L_{SCE}$     |                                    |        | 20   |      | nH   |
| Module lead resistance, terminals - chip | $R_{CC'+EE'}$ | $T_H = 25 \text{ °C}$ , per switch |        | 4    |      | mΩ   |
| Storage temperature                      | $T_{stg}$     |                                    | -40    |      | 125  | °C   |
| Mounting force per clamp                 | $F$           |                                    | 40     | -    | 80   | N    |
| Weight                                   | $G$           |                                    |        | 39   |      | g    |

Note: The current under continuous operation is limited to 25 A rms per connector pin.

## 2 IGBT, Inverter

**Table 3** Maximum rated values

| Parameter                         | Symbol    | Note or test condition               |                          | Values | Unit |
|-----------------------------------|-----------|--------------------------------------|--------------------------|--------|------|
| Collector-emitter voltage         | $V_{CES}$ |                                      | $T_{vj} = 25 \text{ °C}$ | 1200   | V    |
| Implemented collector current     | $I_{CN}$  |                                      |                          | 100    | A    |
| Continuous DC collector current   | $I_{CDC}$ | $T_{vj \max} = 175 \text{ °C}$       | $T_H = 65 \text{ °C}$    | 80     | A    |
| Repetitive peak collector current | $I_{CRM}$ | $t_p$ limited by $T_{vj \text{ op}}$ |                          | 200    | A    |
| Gate-emitter peak voltage         | $V_{GES}$ |                                      |                          | ±20    | V    |

**Table 4**                      **Characteristic values**

| Parameter                            | Symbol        | Note or test condition                                                                                                                         |                          | Values |       |       | Unit     |
|--------------------------------------|---------------|------------------------------------------------------------------------------------------------------------------------------------------------|--------------------------|--------|-------|-------|----------|
|                                      |               |                                                                                                                                                |                          | Min.   | Typ.  | Max.  |          |
| Collector-emitter saturation voltage | $V_{CE\ sat}$ | $I_C = 100\ A, V_{GE} = 15\ V$                                                                                                                 | $T_{vj} = 25\ ^\circ C$  |        | 1.50  | 1.80  | V        |
|                                      |               |                                                                                                                                                | $T_{vj} = 125\ ^\circ C$ |        | 1.64  |       |          |
|                                      |               |                                                                                                                                                | $T_{vj} = 175\ ^\circ C$ |        | 1.72  |       |          |
| Gate threshold voltage               | $V_{GETh}$    | $I_C = 2.5\ mA, V_{CE} = V_{GE}, T_{vj} = 25\ ^\circ C$                                                                                        |                          | 5.15   | 5.80  | 6.45  | V        |
| Gate charge                          | $Q_G$         | $V_{GE} = \pm 15\ V, V_{CC} = 600\ V$                                                                                                          |                          |        | 1.8   |       | $\mu C$  |
| Internal gate resistor               | $R_{Gint}$    | $T_{vj} = 25\ ^\circ C$                                                                                                                        |                          |        | 1.5   |       | $\Omega$ |
| Input capacitance                    | $C_{ies}$     | $f = 100\ kHz, T_{vj} = 25\ ^\circ C, V_{CE} = 25\ V, V_{GE} = 0\ V$                                                                           |                          |        | 21.7  |       | nF       |
| Reverse transfer capacitance         | $C_{res}$     | $f = 100\ kHz, T_{vj} = 25\ ^\circ C, V_{CE} = 25\ V, V_{GE} = 0\ V$                                                                           |                          |        | 0.075 |       | nF       |
| Collector-emitter cut-off current    | $I_{CES}$     | $V_{CE} = 1200\ V, V_{GE} = 0\ V$                                                                                                              | $T_{vj} = 25\ ^\circ C$  |        |       | 0.009 | mA       |
| Gate-emitter leakage current         | $I_{GES}$     | $V_{CE} = 0\ V, V_{GE} = 20\ V, T_{vj} = 25\ ^\circ C$                                                                                         |                          |        |       | 100   | nA       |
| Turn-on delay time (inductive load)  | $t_{don}$     | $I_C = 100\ A, V_{CC} = 600\ V, V_{GE} = \pm 15\ V, R_{Gon} = 1.8\ \Omega$                                                                     | $T_{vj} = 25\ ^\circ C$  |        | 0.150 |       | $\mu s$  |
|                                      |               |                                                                                                                                                | $T_{vj} = 125\ ^\circ C$ |        | 0.166 |       |          |
|                                      |               |                                                                                                                                                | $T_{vj} = 175\ ^\circ C$ |        | 0.174 |       |          |
| Rise time (inductive load)           | $t_r$         | $I_C = 100\ A, V_{CC} = 600\ V, V_{GE} = \pm 15\ V, R_{Gon} = 1.8\ \Omega$                                                                     | $T_{vj} = 25\ ^\circ C$  |        | 0.041 |       | $\mu s$  |
|                                      |               |                                                                                                                                                | $T_{vj} = 125\ ^\circ C$ |        | 0.045 |       |          |
|                                      |               |                                                                                                                                                | $T_{vj} = 175\ ^\circ C$ |        | 0.047 |       |          |
| Turn-off delay time (inductive load) | $t_{doff}$    | $I_C = 100\ A, V_{CC} = 600\ V, V_{GE} = \pm 15\ V, R_{Goff} = 1.8\ \Omega$                                                                    | $T_{vj} = 25\ ^\circ C$  |        | 0.300 |       | $\mu s$  |
|                                      |               |                                                                                                                                                | $T_{vj} = 125\ ^\circ C$ |        | 0.380 |       |          |
|                                      |               |                                                                                                                                                | $T_{vj} = 175\ ^\circ C$ |        | 0.420 |       |          |
| Fall time (inductive load)           | $t_f$         | $I_C = 100\ A, V_{CC} = 600\ V, V_{GE} = \pm 15\ V, R_{Goff} = 1.8\ \Omega$                                                                    | $T_{vj} = 25\ ^\circ C$  |        | 0.100 |       | $\mu s$  |
|                                      |               |                                                                                                                                                | $T_{vj} = 125\ ^\circ C$ |        | 0.180 |       |          |
|                                      |               |                                                                                                                                                | $T_{vj} = 175\ ^\circ C$ |        | 0.250 |       |          |
| Turn-on energy loss per pulse        | $E_{on}$      | $I_C = 100\ A, V_{CC} = 600\ V, L_\sigma = 35\ nH, V_{GE} = \pm 15\ V, R_{Gon} = 1.8\ \Omega, di/dt = 1700\ A/\mu s (T_{vj} = 175\ ^\circ C)$  | $T_{vj} = 25\ ^\circ C$  |        | 6     |       | mJ       |
|                                      |               |                                                                                                                                                | $T_{vj} = 125\ ^\circ C$ |        | 8.4   |       |          |
|                                      |               |                                                                                                                                                | $T_{vj} = 175\ ^\circ C$ |        | 10.1  |       |          |
| Turn-off energy loss per pulse       | $E_{off}$     | $I_C = 100\ A, V_{CC} = 600\ V, L_\sigma = 35\ nH, V_{GE} = \pm 15\ V, R_{Goff} = 1.8\ \Omega, dv/dt = 2850\ V/\mu s (T_{vj} = 175\ ^\circ C)$ | $T_{vj} = 25\ ^\circ C$  |        | 6     |       | mJ       |
|                                      |               |                                                                                                                                                | $T_{vj} = 125\ ^\circ C$ |        | 9.6   |       |          |
|                                      |               |                                                                                                                                                | $T_{vj} = 175\ ^\circ C$ |        | 12    |       |          |

**(table continues...)**

**Table 4** (continued) Characteristic values

| Parameter                                    | Symbol      | Note or test condition                                                                                 | Values |       |      | Unit             |
|----------------------------------------------|-------------|--------------------------------------------------------------------------------------------------------|--------|-------|------|------------------|
|                                              |             |                                                                                                        | Min.   | Typ.  | Max. |                  |
| SC data                                      | $I_{SC}$    | $V_{GE} \leq 15 \text{ V}$ , $V_{CC} = 800 \text{ V}$ ,<br>$V_{CEmax} = V_{CES} - L_{sCE} \cdot di/dt$ |        | 370   |      | A                |
|                                              |             |                                                                                                        |        |       |      |                  |
|                                              |             | $t_p \leq 8 \mu\text{s}$ ,<br>$T_{vj} = 150^\circ\text{C}$                                             |        |       |      |                  |
|                                              |             | $t_p \leq 7 \mu\text{s}$ ,<br>$T_{vj} = 175^\circ\text{C}$                                             |        | 350   |      |                  |
| Thermal resistance,<br>junction to heat sink | $R_{thJH}$  | per IGBT, $\lambda_{grease} = 1 \text{ W/(m}\cdot\text{K)}$                                            |        | 0.700 |      | K/W              |
| Temperature under<br>switching conditions    | $T_{vj op}$ |                                                                                                        | -40    |       | 175  | $^\circ\text{C}$ |

Note:  $T_{vj op} > 150^\circ\text{C}$  is allowed for operation at overload conditions. For detailed specifications, please refer to AN 2018-14.

### 3 Diode, Inverter

**Table 5** Maximum rated values

| Parameter                       | Symbol    | Note or test condition                      | Values                       | Unit                 |
|---------------------------------|-----------|---------------------------------------------|------------------------------|----------------------|
| Repetitive peak reverse voltage | $V_{RRM}$ | $T_{vj} = 25^\circ\text{C}$                 | 1200                         | V                    |
| Continuous DC forward current   | $I_F$     |                                             | 100                          | A                    |
| Repetitive peak forward current | $I_{FRM}$ | $t_p = 1 \text{ ms}$                        | 200                          | A                    |
| $I^2t$ - value                  | $I^2t$    | $t_p = 10 \text{ ms}$ , $V_R = 0 \text{ V}$ | $T_{vj} = 125^\circ\text{C}$ | $\text{A}^2\text{s}$ |
|                                 |           |                                             | $T_{vj} = 175^\circ\text{C}$ |                      |

**Table 6** Characteristic values

| Parameter                     | Symbol   | Note or test condition                                                                                                                                    | Values                       |      |      | Unit |
|-------------------------------|----------|-----------------------------------------------------------------------------------------------------------------------------------------------------------|------------------------------|------|------|------|
|                               |          |                                                                                                                                                           | Min.                         | Typ. | Max. |      |
| Forward voltage               | $V_F$    | $I_F = 100 \text{ A}$ , $V_{GE} = 0 \text{ V}$                                                                                                            | $T_{vj} = 25^\circ\text{C}$  | 1.72 | 2.10 | V    |
|                               |          |                                                                                                                                                           | $T_{vj} = 125^\circ\text{C}$ | 1.59 |      |      |
|                               |          |                                                                                                                                                           | $T_{vj} = 175^\circ\text{C}$ | 1.52 |      |      |
| Peak reverse recovery current | $I_{RM}$ | $V_{CC} = 600 \text{ V}$ , $I_F = 100 \text{ A}$ ,<br>$V_{GE} = -15 \text{ V}$ , $-di_F/dt = 1700 \text{ A}/\mu\text{s}$ ( $T_{vj} = 175^\circ\text{C}$ ) | $T_{vj} = 25^\circ\text{C}$  | 60   |      | A    |
|                               |          |                                                                                                                                                           | $T_{vj} = 125^\circ\text{C}$ | 79   |      |      |
|                               |          |                                                                                                                                                           | $T_{vj} = 175^\circ\text{C}$ | 91   |      |      |

(table continues...)

**Table 6** (continued) Characteristic values

| Parameter                                 | Symbol             | Note or test condition                                                                                                                                             | Values                                |       |      | Unit             |
|-------------------------------------------|--------------------|--------------------------------------------------------------------------------------------------------------------------------------------------------------------|---------------------------------------|-------|------|------------------|
|                                           |                    |                                                                                                                                                                    | Min.                                  | Typ.  | Max. |                  |
| Recovered charge                          | $Q_r$              | $V_{CC} = 600 \text{ V}$ , $I_F = 100 \text{ A}$ ,<br>$V_{GE} = -15 \text{ V}$ , $-di_F/dt = 1700 \text{ A}/\mu\text{s}$ ( $T_{vj} = 175 \text{ }^\circ\text{C}$ ) | $T_{vj} = 25 \text{ }^\circ\text{C}$  | 7.1   |      | $\mu\text{C}$    |
|                                           |                    |                                                                                                                                                                    | $T_{vj} = 125 \text{ }^\circ\text{C}$ | 12.7  |      |                  |
|                                           |                    |                                                                                                                                                                    | $T_{vj} = 175 \text{ }^\circ\text{C}$ | 17.3  |      |                  |
| Reverse recovery energy                   | $E_{rec}$          | $V_{CC} = 600 \text{ V}$ , $I_F = 100 \text{ A}$ ,<br>$V_{GE} = -15 \text{ V}$ , $-di_F/dt = 1700 \text{ A}/\mu\text{s}$ ( $T_{vj} = 175 \text{ }^\circ\text{C}$ ) | $T_{vj} = 25 \text{ }^\circ\text{C}$  | 2.4   |      | mJ               |
|                                           |                    |                                                                                                                                                                    | $T_{vj} = 125 \text{ }^\circ\text{C}$ | 3.9   |      |                  |
|                                           |                    |                                                                                                                                                                    | $T_{vj} = 175 \text{ }^\circ\text{C}$ | 5.6   |      |                  |
| Thermal resistance, junction to heat sink | $R_{thJH}$         | per diode, $\lambda_{grease} = 1 \text{ W}/(\text{m}\cdot\text{K})$                                                                                                |                                       | 0.966 |      | K/W              |
| Temperature under switching conditions    | $T_{vj\text{ op}}$ |                                                                                                                                                                    | -40                                   |       | 175  | $^\circ\text{C}$ |

Note:  $T_{vj\text{ op}} > 150^\circ\text{C}$  is allowed for operation at overload conditions. For detailed specifications, please refer to AN 2018-14.

## 4 NTC-Thermistor

**Table 7** Characteristic values

| Parameter              | Symbol       | Note or test condition                                                   | Values |      |      | Unit       |
|------------------------|--------------|--------------------------------------------------------------------------|--------|------|------|------------|
|                        |              |                                                                          | Min.   | Typ. | Max. |            |
| Rated resistance       | $R_{25}$     | $T_{NTC} = 25 \text{ }^\circ\text{C}$                                    |        | 5    |      | k $\Omega$ |
| Deviation of $R_{100}$ | $\Delta R/R$ | $T_{NTC} = 100 \text{ }^\circ\text{C}$ , $R_{100} = 493 \text{ } \Omega$ | -5     |      | 5    | %          |
| Power dissipation      | $P_{25}$     | $T_{NTC} = 25 \text{ }^\circ\text{C}$                                    |        |      | 20   | mW         |
| B-value                | $B_{25/50}$  | $R_2 = R_{25} \exp[B_{25/50}(1/T_2 - 1/(298,15 \text{ K}))]$             |        | 3375 |      | K          |
| B-value                | $B_{25/80}$  | $R_2 = R_{25} \exp[B_{25/80}(1/T_2 - 1/(298,15 \text{ K}))]$             |        | 3411 |      | K          |
| B-value                | $B_{25/100}$ | $R_2 = R_{25} \exp[B_{25/100}(1/T_2 - 1/(298,15 \text{ K}))]$            |        | 3433 |      | K          |

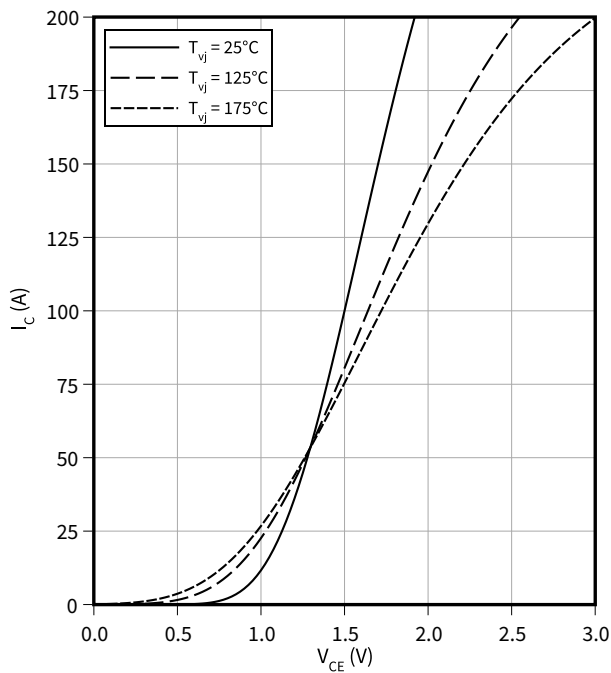
Note: Specification according to the valid application note.

5 Characteristics diagrams

Output characteristic (typical), IGBT, Inverter

$I_C = f(V_{CE})$

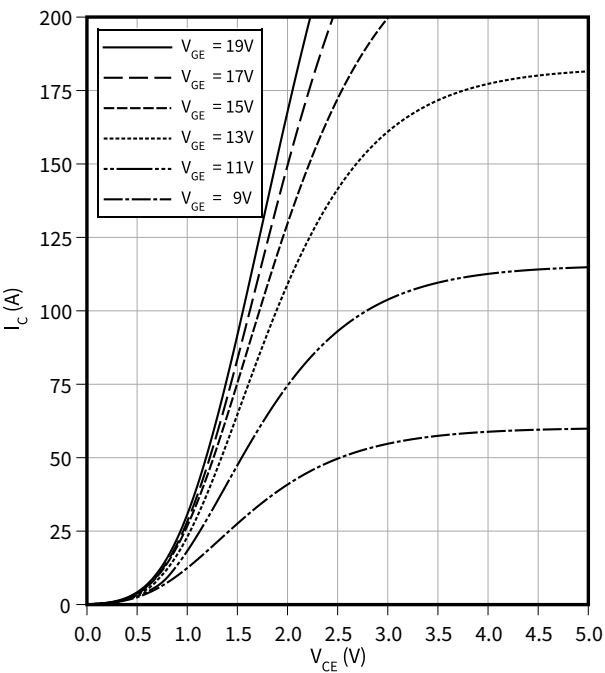
$V_{GE} = 15\text{ V}$



Output characteristic field (typical), IGBT, Inverter

$I_C = f(V_{CE})$

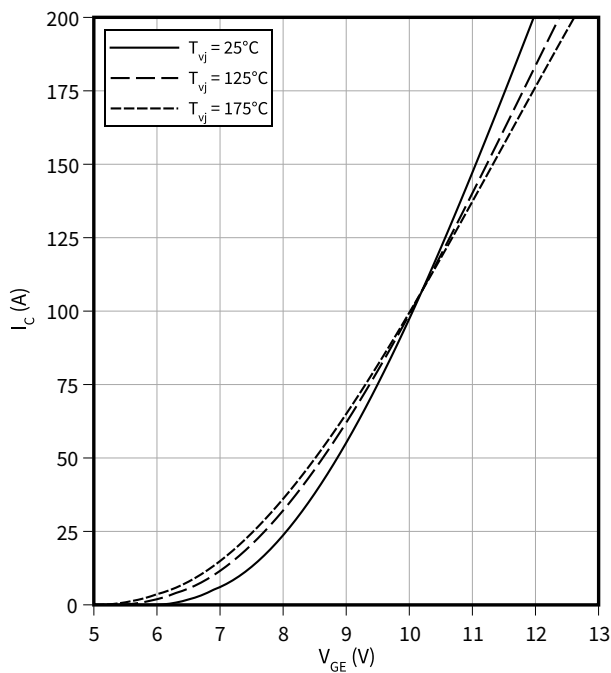
$T_{vj} = 175^\circ\text{C}$



Transfer characteristic (typical), IGBT, Inverter

$I_C = f(V_{GE})$

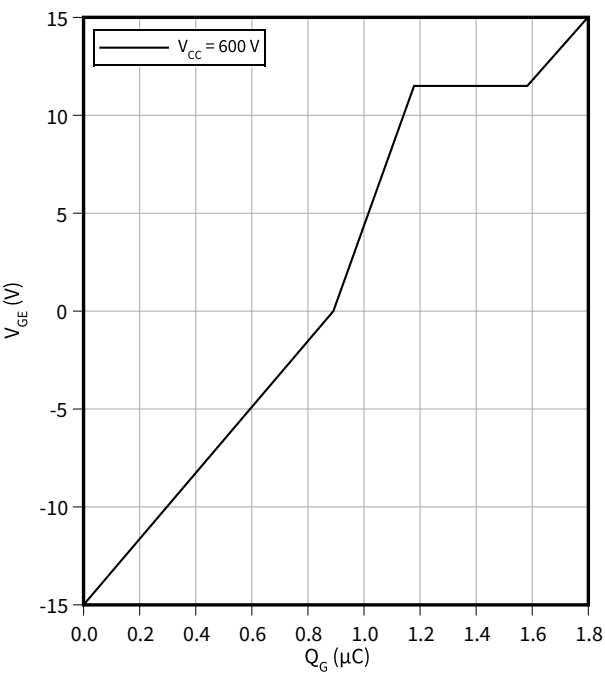
$V_{CE} = 20\text{ V}$



Gate charge characteristic (typical), IGBT, Inverter

$V_{GE} = f(Q_G)$

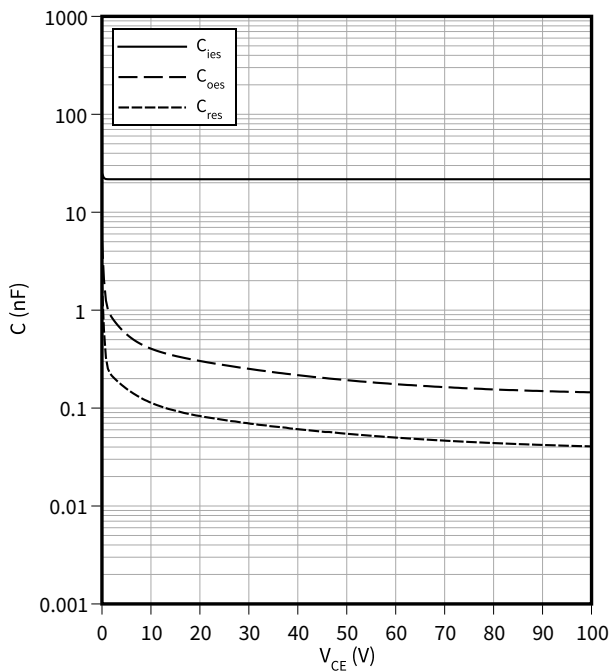
$I_C = 100\text{ A}, T_{vj} = 25^\circ\text{C}$



5 Characteristics diagrams

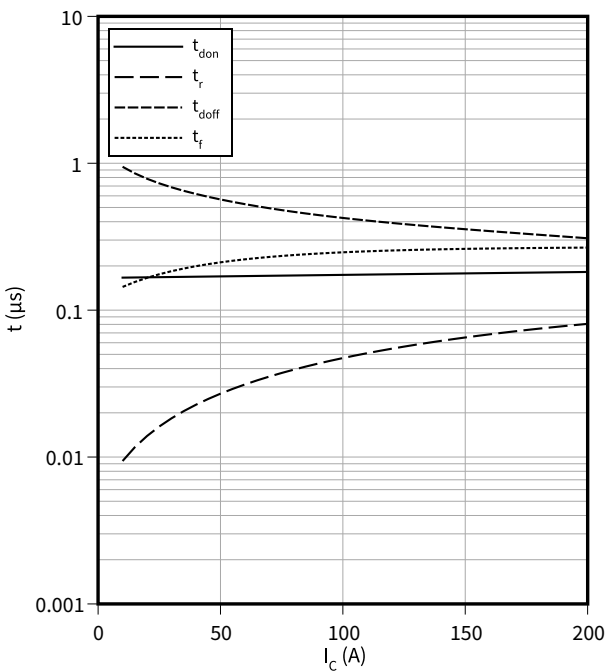
Capacity characteristic (typical), IGBT, Inverter

$C = f(V_{CE})$   
 $V_{GE} = 0\text{ V}$ ,  $f = 100\text{ kHz}$ ,  $T_{vj} = 25\text{ °C}$



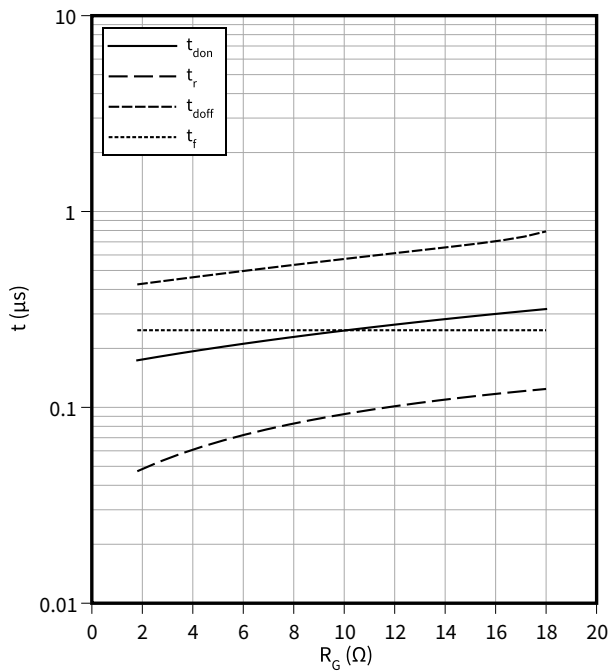
Switching times (typical), IGBT, Inverter

$t = f(I_C)$   
 $R_{Goff} = 1.8\text{ }\Omega$ ,  $R_{Gon} = 1.8\text{ }\Omega$ ,  $V_{CC} = 600\text{ V}$ ,  $V_{GE} = \pm 15\text{ V}$ ,  $T_{vj} = 175\text{ °C}$



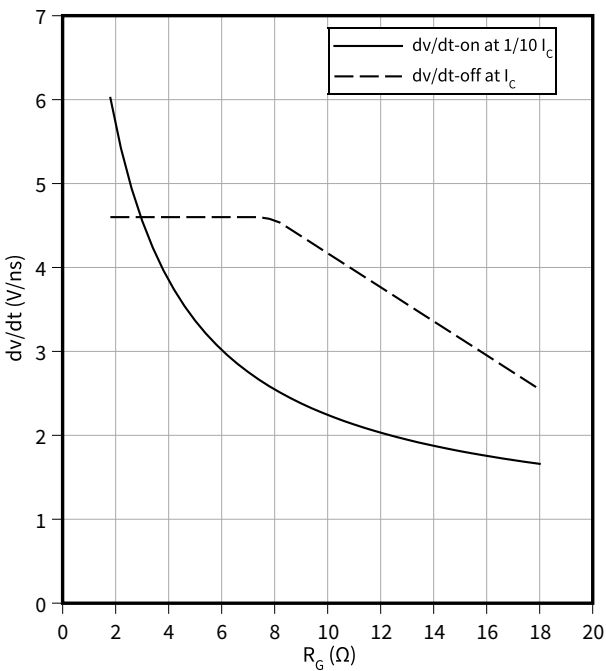
Switching times (typical), IGBT, Inverter

$t = f(R_G)$   
 $I_C = 100\text{ A}$ ,  $V_{CC} = 600\text{ V}$ ,  $V_{GE} = \pm 15\text{ V}$ ,  $T_{vj} = 175\text{ °C}$



Voltage slope (typical), IGBT, Inverter

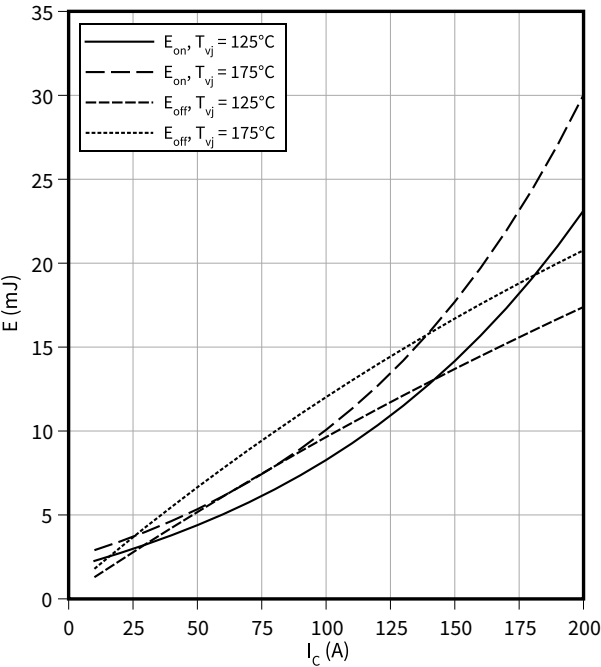
$dv/dt = f(R_G)$   
 $I_C = 100\text{ A}$ ,  $V_{CC} = 600\text{ V}$ ,  $V_{GE} = \pm 15\text{ V}$ ,  $T_{vj} = 25\text{ °C}$



5 Characteristics diagrams

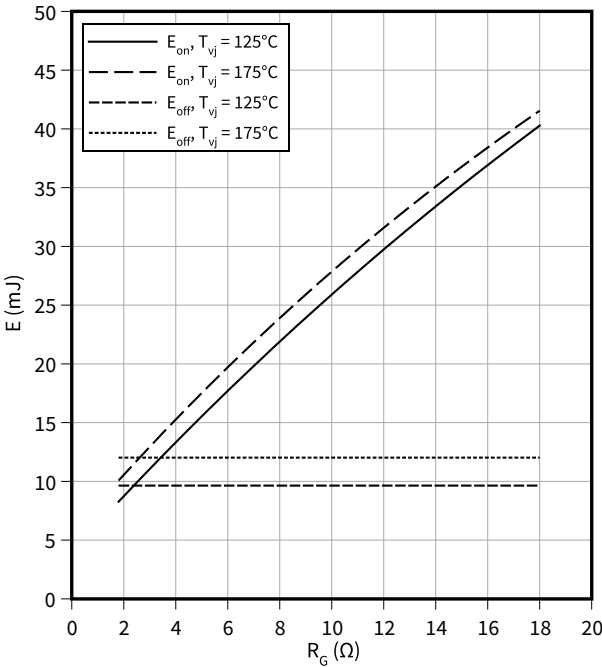
Switching losses (typical), IGBT, Inverter

$E = f(I_C)$   
 $R_{Goff} = 1.8 \Omega$ ,  $R_{Gon} = 1.8 \Omega$ ,  $V_{CC} = 600 \text{ V}$ ,  $V_{GE} = \pm 15 \text{ V}$



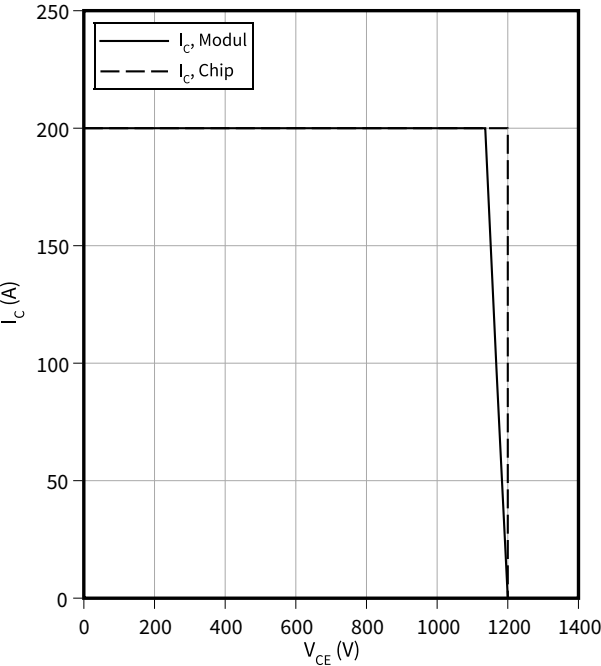
Switching losses (typical), IGBT, Inverter

$E = f(R_G)$   
 $I_C = 100 \text{ A}$ ,  $V_{CC} = 600 \text{ V}$ ,  $V_{GE} = \pm 15 \text{ V}$



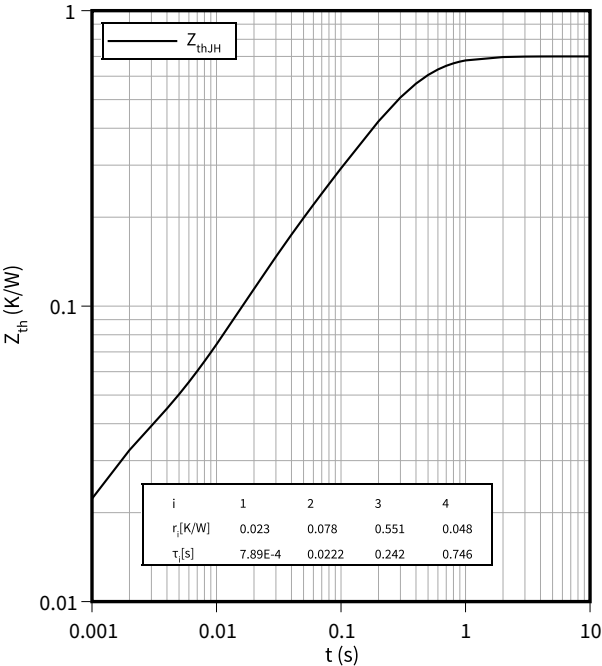
Reverse bias safe operating area (RBSOA), IGBT, Inverter

$I_C = f(V_{CE})$   
 $R_{Goff} = 1.8 \Omega$ ,  $V_{GE} = \pm 15 \text{ V}$ ,  $T_{vj} = 175 \text{ °C}$



Transient thermal impedance, IGBT, Inverter

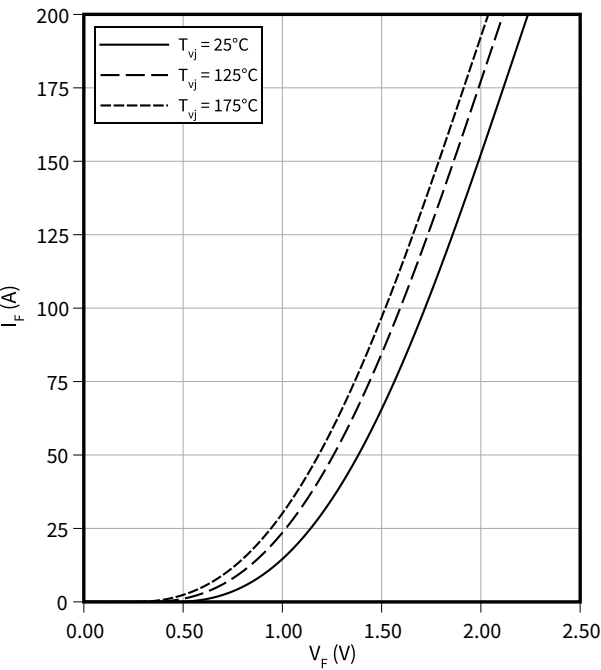
$Z_{th} = f(t)$



5 Characteristics diagrams

Forward characteristic (typical), Diode, Inverter

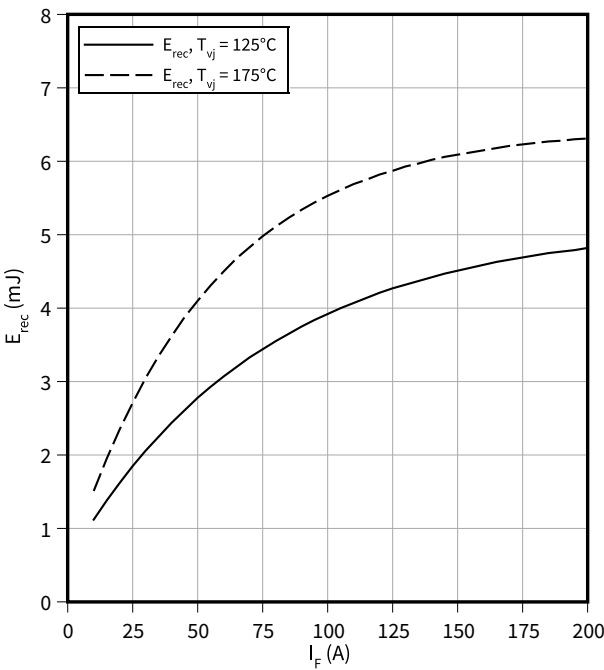
$I_F = f(V_F)$



Switching losses (typical), Diode, Inverter

$E_{rec} = f(I_F)$

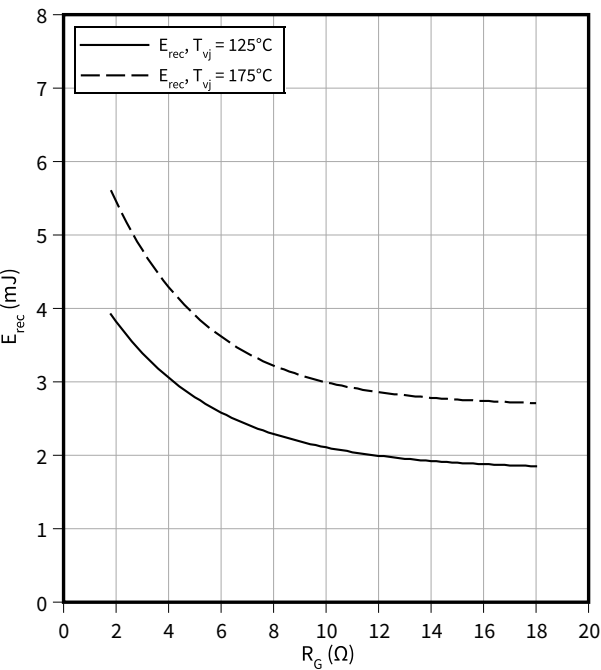
$R_{Gon} = 1.8\ \Omega, V_{CC} = 600\ \text{V}$



Switching losses (typical), Diode, Inverter

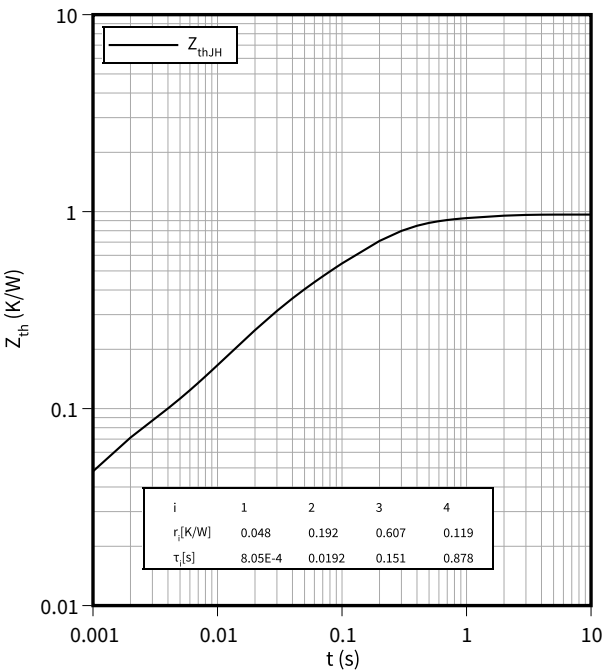
$E_{rec} = f(R_G)$

$I_F = 100\ \text{A}, V_{CC} = 600\ \text{V}$



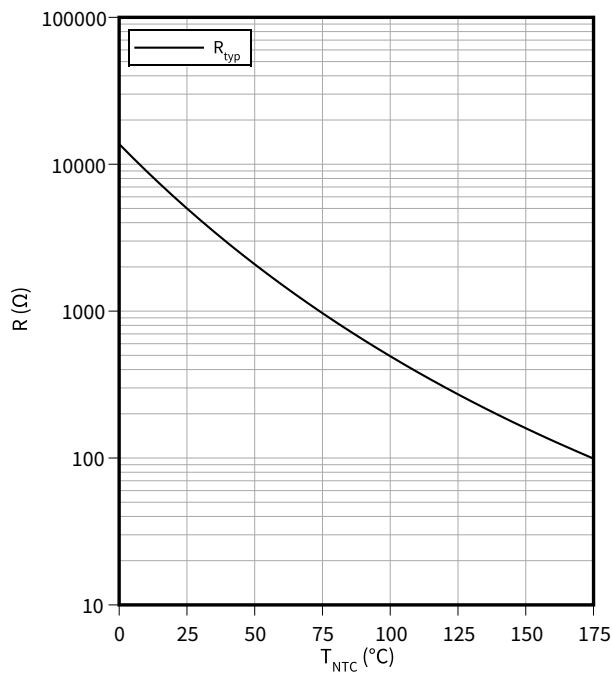
Transient thermal impedance, Diode, Inverter

$Z_{th} = f(t)$



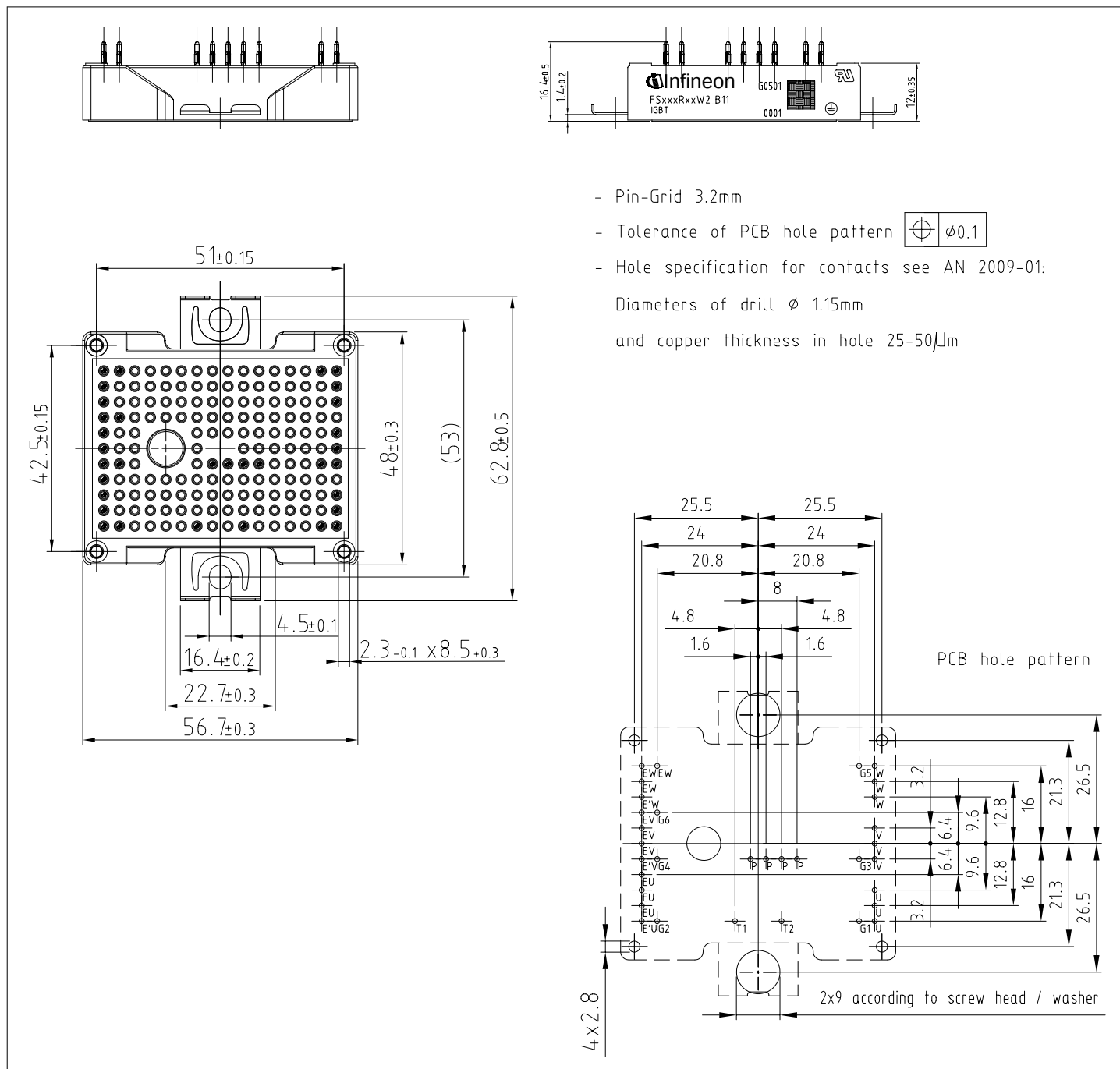
Temperature characteristic (typical), NTC-Thermistor

$R = f(T_{NTC})$



### Figure 1

## 7 Package outlines



**Figure 2**

8 Module label code

| Module label code       |                                                                                     |                         |                 |
|-------------------------|-------------------------------------------------------------------------------------|-------------------------|-----------------|
| Code format             | Data Matrix                                                                         |                         | Barcode Code128 |
| Encoding                | ASCII text                                                                          |                         | Code Set A      |
| Symbol size             | 16x16                                                                               |                         | 23 digits       |
| Standard                | IEC24720 and IEC16022                                                               |                         | IEC8859-1       |
| Code content            | <i>Content</i>                                                                      | <i>Digit</i>            | <i>Example</i>  |
|                         | Module serial number                                                                | 1 – 5                   | 71549           |
|                         | Module material number                                                              | 6 - 11                  | 142846          |
|                         | Production order number                                                             | 12 - 19                 | 55054991        |
|                         | Date code (production year)                                                         | 20 – 21                 | 15              |
|                         | Date code (production week)                                                         | 22 – 23                 | 30              |
| Example                 |   |                         |                 |
|                         |  |                         |                 |
| 71549142846550549911530 |                                                                                     | 71549142846550549911530 |                 |

Figure 3

## Revision history

| Document revision | Date of release | Description of changes                                                                                                                              |
|-------------------|-----------------|-----------------------------------------------------------------------------------------------------------------------------------------------------|
| V1.0              | 2018-01-15      | Target datasheet                                                                                                                                    |
| V1.1              | 2018-06-07      | Target datasheet                                                                                                                                    |
| V2.0              | 2018-08-30      | Preliminary datasheet                                                                                                                               |
| V2.1              | 2018-12-03      | Preliminary datasheet                                                                                                                               |
| n/a               | 2020-09-01      | Datasheet migrated to a new system with a new layout and new revision number schema: target or preliminary datasheet = 0.xy; final datasheet = 1.xy |
| 1.00              | 2023-05-19      | Final datasheet                                                                                                                                     |

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